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Integrated circuits based on bilayer MoS₂ transistors

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1433	Raman spectroscopy of the interlayer shear mode in few-layer MoS ₂ flakes. 2012 , 101, 101906		148
1432	Electronics and optoelectronics of two-dimensional transition metal dichalcogenides. 2012 , 7, 699-712		10871
1431	Field-effect transistors and intrinsic mobility in ultra-thin MoSe ₂ layers. 2012 , 101, 223104		414
1430	Large-scale 2D electronics based on single-layer MoS ₂ grown by chemical vapor deposition. 2012 ,		40
1429	Selective Adsorption of Thiol Molecules at Sulfur Vacancies on MoS ₂ (0001), Followed by Vacancy Repair via S ₂ Dissociation. 2012 , 116, 22411-22416		112
1428	Stepping up MoS ₂ integration. 2012 , 11, 829-829		4
1427	Elucidating the Photoresponse of Ultrathin MoS ₂ Field-Effect Transistors by Scanning Photocurrent Microscopy. 2013 , 4, 2508-2513		169
1426	Thickness-dependent interfacial Coulomb scattering in atomically thin field-effect transistors. <i>Nano Letters</i> , 2013 , 13, 3546-52	11.5	236
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1424	Joined edges in MoS ₂ : metallic and half-metallic wires. 2013 , 25, 312201		16
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1403	Atomistic full-band simulations of monolayer MoS ₂ transistors. 2013 , 103, 223509	42
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